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(21)Application number : 62-181922 (71)Applicant : FUJITSU LTD

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(54) THIN FILM TRANSISTOR MATRIX

(57)Abstract:

PURPOSE: To suppress the fluctuation in the voltage of picture element electrodes by capacity coupling so that a sharp image is obtd. by forming an opaque conductive film coated on a drain bus line, gate bus line and thin film transistor via a protective insulating film.

CONSTITUTION: The opaque conductive film 7 is formed via the protective insulating film 6 on the drain bus line 2, gate bus line 3 and thin film transistor (TFT) 4 formed on an insulating substrate such as glass substrate 1. Namely, the potential conductive film 7 acts as a shielding film between the picture element electrode 5 and the drain bus line 2 if the conductive film 7 is connected to a ground end. The capacity component is then eliminated from the parasitic capacity and only the capacity component CD32 between the rear faces is eventually made to remain. The influence of the potential of the drain bus line 2 on the potential of the picture element electrode 5 is, thereby, extremely

minimized. The undesirable fluctuation in the voltages is thereby suppressed and the good image quality is obtd.

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